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(71) Applicant (for all designated States except US): CANON KABUSHIKI KAISHA [JP/JP]; 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 1468501 (JP).

(72) Inventors; and

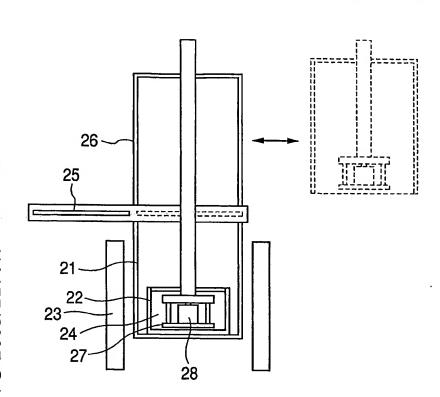
(75) Inventors/Applicants (for US only): MIZUTANI, Masaki [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 1468501 (JP). NISHIDA, Shoji [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku,

1468501 (JP). NAKAGAWA, Katsumi [JP/JP]; c/o CANON KABUSHIKI KAISHA, 3-30-2, Shimomaruko, Ohta-ku, Tokyo, 1468501 (JP).

- (74) Agents: OKABE, Masao et al.; No.602, Fiji Building, 2-3, Marunouchi 3-chome, Chiyoda-ku, Tokyo 100-0005 (JP).
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(54) Title: SILICON LAYER PRODUCTION METHOD AND SOLAR CELL PRODUCTION METHOD



(57) Abstract: A solar cell is produced by dipping a multicrystalline silicon substrate 28 in a solution 24 containing silicon, growing a silicon layer on the substrate 28 while decreasing with time the temperature drop rate of the solution during the dipping of the substrate in the solution, and forming a pn junction in the silicon layer. Thereby, there is provided a silicon layer production method that can form a thick layer while restraining the degree of roughness, whereby a low-cost, multicrystalline-silicon solar cell production method is provided that realizes both a large current and a high FF.

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